

abandonment of this application, then such extensions of time are hereby petitioned under 37 C.F.R. § 1.136(a), and any fees required therefor (including fees for net addition of claims) are hereby authorized to be charged to our Deposit Account No. 19-0036.

*Amendments*

*In the Specification:*

Substitute the paragraph beginning on page 1, line 25, with the following paragraph:

Q1 The dielectric material separating the polysilicon gate from the channel region, henceforth referred to as the gate oxide, usually consists of the thermally grown silicon dioxide (SiO<sub>2</sub>) material that leaks very little current through a mechanism called Fowler-Nordheim tunneling under voltage stress. When stressed beyond a critical electrical field (applied voltage divided by the thickness of the oxide), the transistor is destroyed by rupturing of the oxide.

Substitute the paragraph beginning on page 5, line 28, with the following paragraph:

Q2 FIG. 1 illustrates a block diagram of a one-time programmable storage cell and ancillary circuitry, according to the present invention. The block diagram of FIG. 1 includes a storage cell 102, and a write circuit 104, a read circuit 106 and a current bias and voltage clamp circuit 108.

Substitute the paragraph beginning on page 6, line 25, with the following paragraph:

Q3 <sup>Sub C10</sup> ~~Read is coupled between the vload node and switches 212 and 214 via a connection labeled "n3v5out" (negative 3.5 volt out). Closing of write switches~~

Sub  
C10  
93

206 and 214, while read switches 208, 210 and 212 remain open, permits sufficient current to flow through the vload node to rupture the anti-fuse. Once programmed in this manner, the anti-fuse can be read by read circuit 106. In this arrangement, write switch 206 must have a voltage tolerance higher than that of the anti-fuse. To achieve this higher voltage tolerance, the switches, including write switch 206, are formed with thicker gate oxide layers (e.g., 50-70  $\mu\text{m}$ ).

---